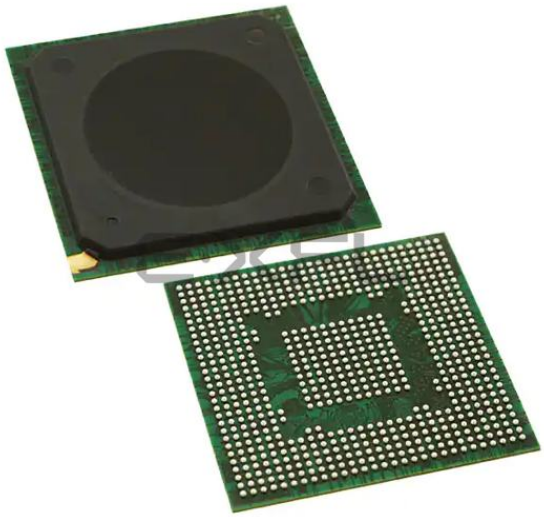

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c4s
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	Security; SEC 3.0
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 125°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	689-BBGA Exposed Pad
Supplier Device Package	689-TEPBGA II (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8377evralga

There are two I^2C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. 16-byte FIFOs are supported for both the transmitter and the receiver.

The main component of the enhanced local bus controller (eLBC) is its memory controller, which provides a seamless interface to many types of memory devices and peripherals. The memory controller is responsible for controlling eight memory banks shared by a NAND Flash control machine (FCM), a general-purpose chip-select machine (GPCM), and up to three user-programmable machines (UPMs). As such, it supports a minimal glue logic interface to SRAM, EPROM, NOR Flash EPROM, NAND Flash, EPROM, burstable RAM, regular DRAM devices, extended data output DRAM devices, and other peripherals. The eLBC external address latch enable (LALE) signal allows multiplexing of addresses with data signals to reduce the device pin count.

The enhanced local bus controller also includes a number of data checking and protection features, such as data parity generation and checking, write protection, and a bus monitor to ensure that each bus cycle is terminated within a user-specified period. The local bus can operate at up to 133 MHz.

The system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

1.8 Security Engine

The optional security engine is optimized to handle all the algorithms associated with IPSec, IEEE 802.11i, and iSCSI. The security engine contains one crypto-channel, a controller, and a set of crypto execution units (EUs). The execution units are as follows:

- Data encryption standard execution unit (DEU), supporting DES and 3DES
- Advanced encryption standard unit (AESU), supporting AES
- Message digest execution unit (MDEU), supporting MD5, SHA1, SHA-256, and HMAC with any algorithm
- One crypto-channel supporting multi-command descriptor chains

1.9 PCI Controller

The PCI controller includes the following features:

- *PCI Specification Revision 2.3* compatible
- Single 32-bit data PCI interface operates at up to 66 MHz
- PCI 3.3-V compatible (not 5-V compatible)
- Support for host and agent modes
- On-chip arbitration, supporting 5 external masters on PCI
- Selectable hardware-enforced coherency

Table 5. Power Dissipation [1] (continued)

Core Frequency (MHz)	CSB/DDR Frequency (MHz)	Sleep Power at T_j = 65°C (W) [2]	Typical Application at T_j = 65°C (W) [2]	Typical Application at T_j = 125°C (W) [3]	Max Application at T_j = 125°C (W) [4]
600	400	1.45	2.1	3.4	4.1
	300	1.45	2.0	3.3	4.0
667	333	1.45	2.1	3.3	4.1
	266	1.45	2.0	3.3	3.9
800	400	1.45	2.5	3.8	4.3

Notes:
1. The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 6.
2. Typical power is based on a voltage of V_{DD} = 1.0 V for core frequencies ≤ 667 MHz or V_{DD} = 1.05 V for core frequencies of 800 MHz, and running a Dhrystone benchmark application.
3. Typical power is based on a voltage of V_{DD} = 1.0 V for core frequencies ≤ 667 MHz or V_{DD} = 1.05 V for core frequencies of 800 MHz, and running a Dhrystone benchmark application.
4. Maximum power is based on a voltage of V_{DD} = 1.0 V for core frequencies ≤ 667 MHz or V_{DD} = 1.05 V for core frequencies of 800 MHz, worst case process, and running an artificial smoke test.

This table shows the estimated typical I/O power dissipation for the device.

Table 6. Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD}/LBV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	L[1,2]_$n$$V_{DD}$ (1.0 V)	Unit	Comments
DDR I/O 65% utilization 2 pair of clocks	200 MHz data rate, 32-bit	0.28	0.35	—	—	—	—	W	—
	200 MHz data rate, 64-bit	0.41	0.49	—	—	—	—	W	
	266 MHz data rate, 32-bit	0.31	0.4	—	—	—	—	W	
	266 MHz data rate, 64-bit	0.46	0.56	—	—	—	—	W	
	300 MHz data rate, 32-bit	0.33	0.43	—	—	—	—	W	
	300 MHz data rate, 64-bit	0.48	0.6	—	—	—	—	W	
	333 MHz data rate, 32-bit	0.35	0.45	—	—	—	—	W	
	333 MHz data rate, 64-bit	0.51	0.64	—	—	—	—	W	
	400 MHz data rate, 32-bit	0.38	—	—	—	—	—	W	
	400 MHz data rate, 64-bit	0.56	—	—	—	—	—	W	

6.1 DDR1 and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2, 5
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.140	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.140	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.40 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.3 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.
5. See AN3665, “MPC837xE Design Checklist,” for proper DDR termination.

Table 14 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM DC Electrical Characteristics for GV_{DD} (typ) = 2.5 V

Parameter	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2, 5
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—

Table 15. DDR SDRAM DC Electrical Characteristics for GV_{DD} (typ) = 2.5 V (continued)

Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.9 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.38 V)	I_{OL}	15.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.
5. See AN3665, “MPC837xE Design Checklist,” for proper DDR termination.

Table 16 provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM Capacitance for GV_{DD} (typ) = 2.5 V

Parameter	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 17. Current Draw Characteristics for MV_{REF}

Parameter	Symbol	Min	Typ	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}				μA	1, 2
DDR1		—	250	600		
DDR2		—	150	400		

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to the stated maximum current.
2. This current is divided equally between MVREF1 and MVREF2, where half the current flows through each pin.

This figure shows the DDR1 and DDR2 SDRAM output timing diagram.

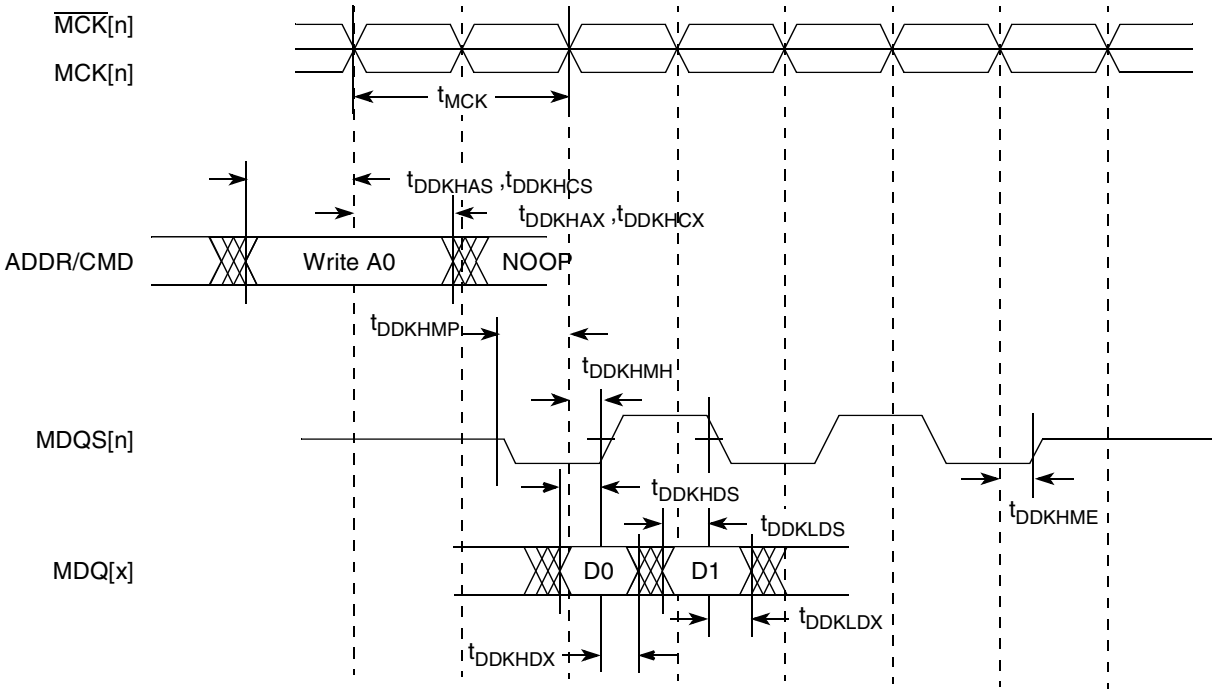

Figure 5. DDR1 and DDR2 SDRAM Output Timing Diagram

This figure provides AC test load for the DDR bus.

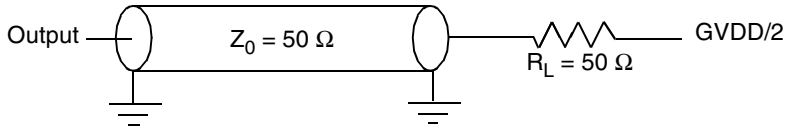

Figure 6. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the chip.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface of the device.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

This table shows the RMII transmit AC timing specifications.

Table 29. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typical	Max	Unit
REF_CLK clock period	t_{RMT}	15.0	20.0	25.0	ns
REF_CLK duty cycle	t_{RMTH}	35	50	65	%
REF_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time REF_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time REF_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns
REF_CLK to RMII data TXD[1:0], TX_EN delay	t_{RMTDX}	2.0	—	10.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.

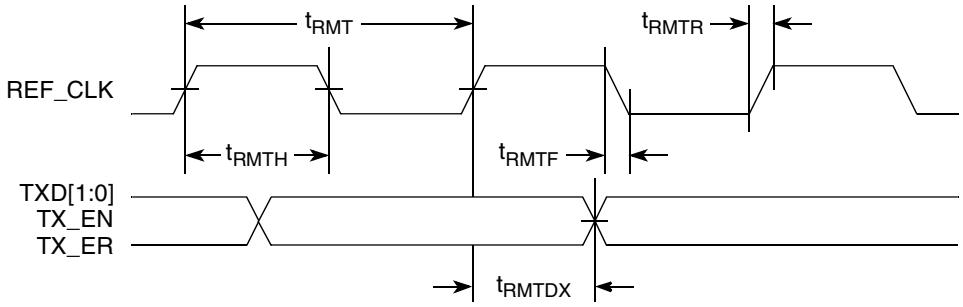

Figure 12. RMII Transmit AC Timing Diagram

8.2.3.2 RMII Receive AC Timing Specifications

This table shows the RMII receive AC timing specifications.

Table 30. RMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
Input low voltage at 3.3 LV_{DD}	V_{IL}	—	—	0.8	V
Input high voltage at 3.3 LV_{DD}	V_{IH}	2.0	—	—	V
REF_CLK clock period	t_{RMR}	15.0	20.0	25.0	ns
REF_CLK duty cycle	t_{RMRH}	35	50	65	%
REF_CLK peak-to-peak jitter	t_{RMRJ}	—	—	250	ps
Rise time REF_CLK (20%–80%)	t_{RMRR}	1.0	—	2.0	ns
Fall time REF_CLK (80%–20%)	t_{RMRF}	1.0	—	2.0	ns
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK rising edge	t_{RMRDV}	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK rising edge	t_{RMRDX}	2.0	—	—	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load for eTSEC.

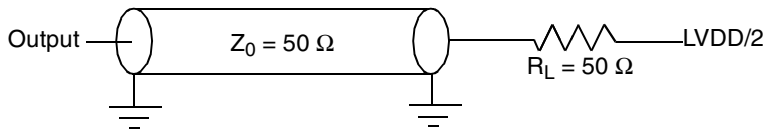

Figure 13. eTSEC AC Test Load

Table 32. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Conditions		Symbol	Min	Max	Unit
Supply voltage (3.3 V)	—		LV_{DD1}	3.135	3.465	V
Output high voltage	I_{OH} = –1.0 mA	LV_{DD1} = Min	V_{OH}	2.10	LV_{DD1} + 0.3	V
Output low voltage	I_{OL} = 1.0 mA	LV_{DD1} = Min	V_{OL}	GND	0.50	V
Input high voltage	—		V_{IH}	2.00	—	V
Input low voltage	—		V_{IL}	—	0.80	V
Input high current	LV_{DD1} = Max	V_{IN} [1] = 2.1 V	I_{IH}	—	30	μA
Input low current	LV_{DD1} = Max	V_{IN} = 0.5 V	I_{IL}	–600	—	μA

8.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 33. MII Management AC Timing Specifications

Parameter	Symbol[1]	Min	Typical	Max	Unit	Note
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	80	—	400	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$2 \times (t_{plb\_clk} \times 8)$	—	—	ns	4
MDC to MDIO delay	t_{MDKHDX}	10	—	$2 \times (t_{plb\_clk} \times 8)$	ns	2, 4
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time (20%–80%)	t_{MDCR}	—	—	10	ns	3
MDC fall time (80%–20%)	t_{MDCF}	—	—	10	ns	3

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the system clock speed.
3. Guaranteed by design.
4. t_{plb_clk} is the platform (CSB) clock divided according to the SCCR[TSEC1CM].

This table describes the general timing parameters of the local bus interface of the device when in PLL bypass mode.

Table 40. Local Bus General Timing Parameters—PLL Bypass Mode

Parameter	Symbol[1]	Min	Max	Unit	Note
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7.0	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3.0	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid	t_{LBKHOV}	—	3.0	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4.0	ns	3, 8

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $LBV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times LBV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when LBCR[AHD] is set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when LBCR[AHD] is not set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when LBCR[AHD] is not set and the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

This figure provides the AC test load for the local bus.

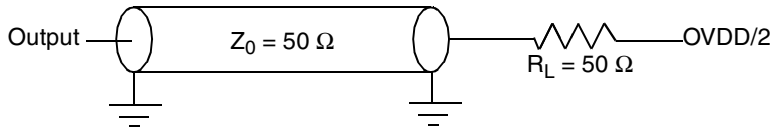

Figure 19. Local Bus AC Test Load

Table 45. JTAG AC Timing Specifications (Independent of CLKIN) [1] (continued)

Parameter	Symbol[2]	Min	Max	Unit	Note
JTAG external clock to output high impedance: Boundary-scan data TDO	 t_{JTKLDZ} t_{JTKLOZ}	 2 2	 19 9	ns	5

Notes:
1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 17). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. $\overline{\text{TRST}}$ is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK}.
5. Non-JTAG signal output timing with respect to t_{TCLK}.

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.

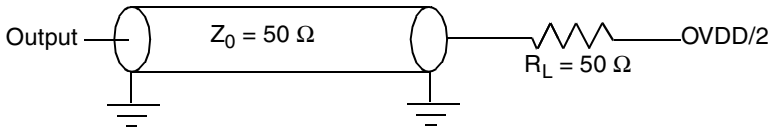

Figure 32. AC Test Load for the JTAG Interface

This figure provides the JTAG clock input timing diagram.

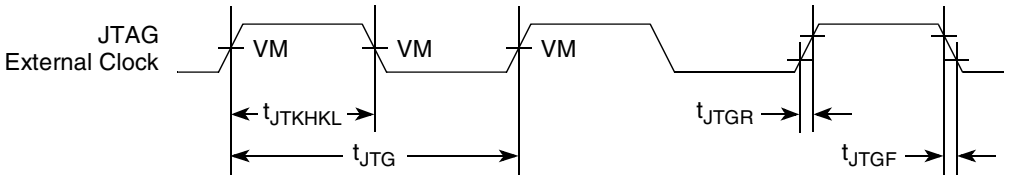

Figure 33. JTAG Clock Input Timing Diagram

This figure provides the $\overline{\text{TRST}}$ timing diagram.

Figure 34. $\overline{\text{TRST}}$ Timing Diagram

This figure provides the boundary-scan timing diagram.

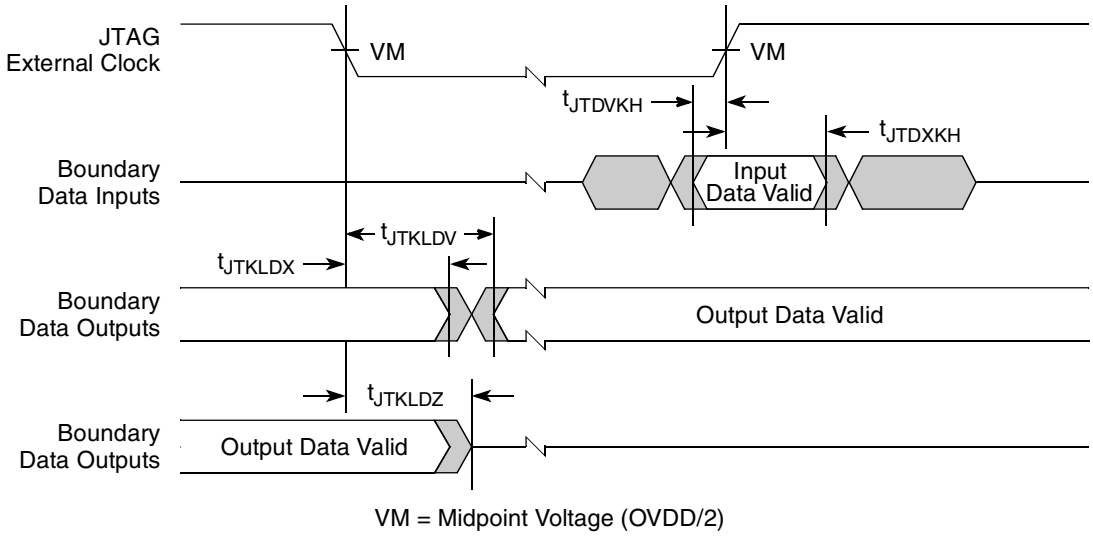

Figure 35. Boundary-Scan Timing Diagram

This figure provides the test access port timing diagram.

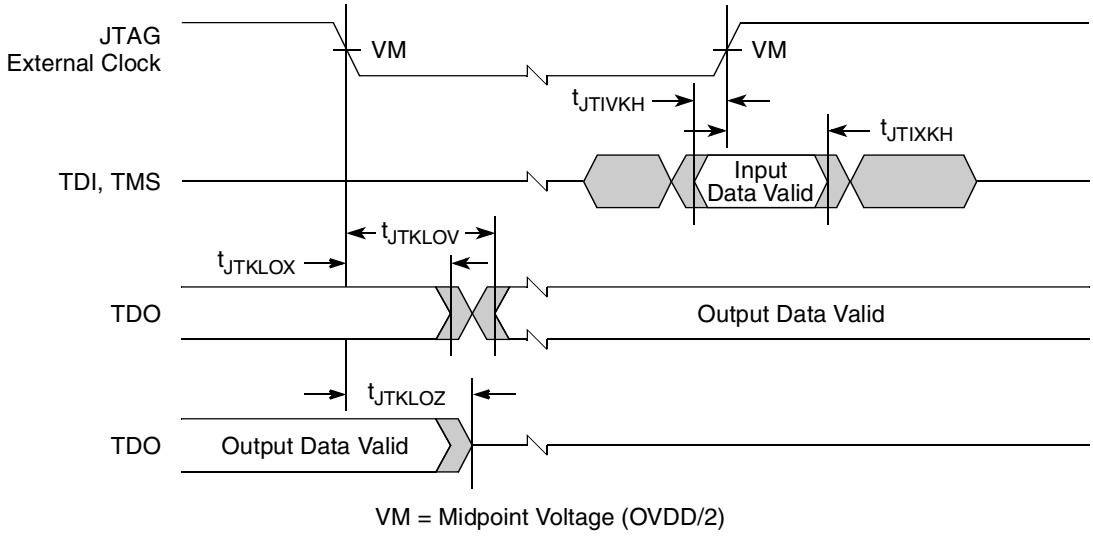

Figure 36. Test Access Port Timing Diagram

This figure provides the AC test load for PCI.

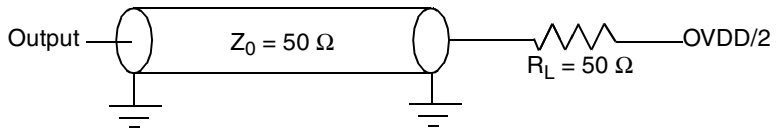

Figure 39. PCI AC Test Load

This figure shows the PCI input AC timing conditions.

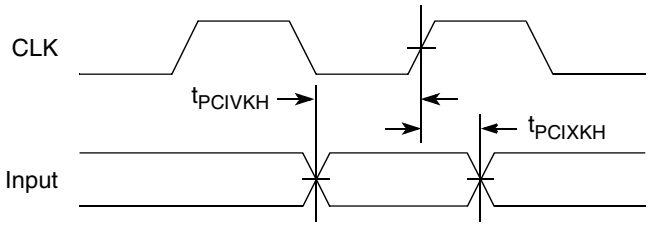

Figure 40. PCI Input AC Timing Measurement Conditions

This figure shows the PCI output AC timing conditions.

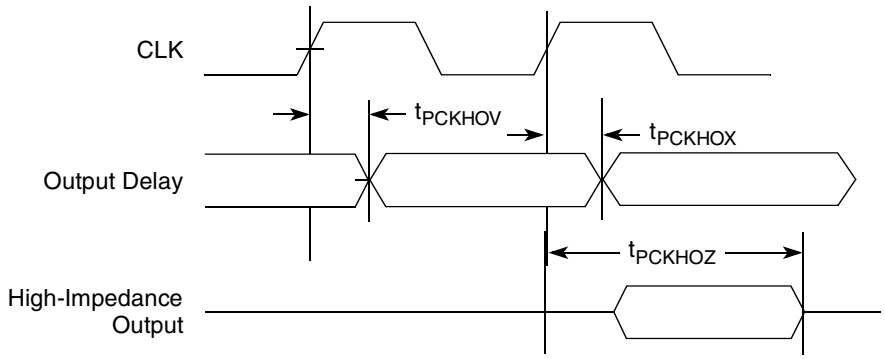

Figure 41. PCI Output AC Timing Measurement Condition

15 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus.

15.1 DC Requirements for PCI Express SD_REF_CLK and SD_REF_CLK

For more information see Section 21, “High-Speed Serial Interfaces (HSSI).”

This table provides the differential transmitter output AC characteristics for the SATA interface at Gen1i or 1.5 Gbits/s transmission.

Table 56. Gen1i/1.5G Transmitter AC Specifications

Parameter	Symbol	Min	Typical	Max	Units	Note
Channel speed	t_{CH_SPEED}	—	1.5	—	Gbps	—
Unit interval	T_{UI}	666.4333	666.667	670.2333	ps	—
Total jitter, data-data 5 UI	$U_{SATA\_TXTJ5UI}$	—	—	0.355	UI_{p-p}	1
Total jitter, data-data 250 UI	$U_{SATA\_TXTJ250UI}$	—	—	0.47	UI_{p-p}	1
Deterministic jitter, data-data 5 UI	$U_{SATA\_TXDJ5UI}$	—	—	0.175	UI_{p-p}	1
Deterministic jitter, data-data 250 UI	$U_{SATA\_TXDJ250UI}$	—	—	0.22	UI_{p-p}	1

Note:
1. Measured at Tx output pins peak to peak phase variation, random data pattern.

16.2.2 Gen2i/3G Transmitter Specifications

This table provides the differential transmitter output DC characteristics for the SATA interface at Gen2i or 3.0 Gbits/s transmission.

Table 57. Gen 2i/3G Transmitter DC Specifications

Parameter	Symbol	Min	Typical	Max	Units	Note
Tx differential output voltage	V_{SATA_TXDIFF}	400	550	700	mV_{p-p}	1
Tx differential pair impedance	$Z_{SATA\_TXDIFFIM}$	85	100	115	Ω	—

Note:
1. Terminated by 50 Ω load.

This table provides the differential transmitter output AC characteristics for the SATA interface at Gen2i or 3.0 Gbits/s transmission.

Table 58. Gen 2i/3G Transmitter AC Specifications

Parameter	Symbol	Min	Typical	Max	Units	Note
Channel speed	t_{CH_SPEED}	—	3.0	—	Gbps	—
Unit interval	T_{UI}	333.2	333.33	335.11	ps	—
Total jitter $f_{C3dB}=f_{BAUD}/10$	$U_{SATA\_TXTJfB/10}$	—	—	0.3	UI_{p-p}	1
Total jitter $f_{C3dB} = f_{BAUD}/500$	$U_{SATA\_TXTJfB/500}$	—	—	0.37	UI_{p-p}	1

Table 69. SPI DC Electrical Characteristics (continued)

Parameter	Condition	Symbol	Min	Max	Unit
Output low voltage	I_{OL} = 8.0 mA	V_{OL}	—	0.5	V
Output low voltage	I_{OL} = 3.2 mA	V_{OL}	—	0.4	V

20.2 SPI AC Timing Specifications

This table provides the SPI input and output AC timing specifications.

Table 70. SPI AC Timing Specifications

Parameter	Symbol[1]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).
2. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin. The maximum SPICLK input frequency is 66.666 MHz.

This figure provides the AC test load for the SPI.

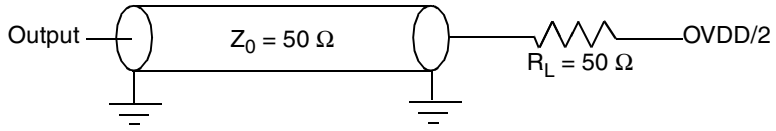

Figure 48. SPI AC Test Load

These figures represent the AC timing from Table 70. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

— The SerDes reference clock input can be either differential or single-ended. Refer to the Differential Mode and Single-ended Mode description below for further detailed requirements.

- The maximum average current requirement that also determines the common mode voltage range
  — When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (refer to the following bullet for more detail), since the input is AC-coupled on-chip.
  — This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V ÷ 50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND_SRDS*n* (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0 mA to 16 mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
  — If the device driving the SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDS*n* (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement
  — This requirement is described in detail in the following sections.

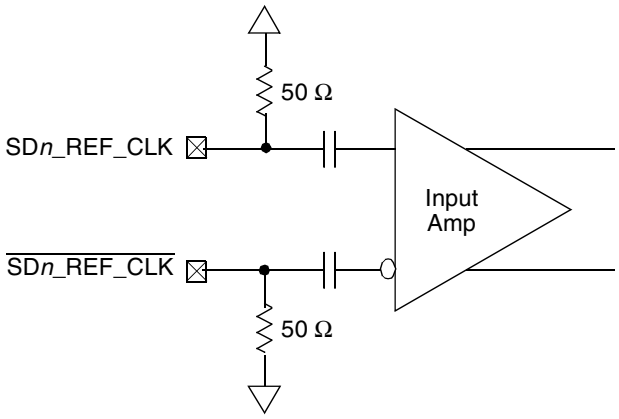

Figure 52. Receiver of SerDes Reference Clocks

21.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the device SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- **Differential Mode**
  — The input amplitude of the differential clock must be between 400 mV and 1600 mV differential peak-peak (or between 200 mV and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800 mV and

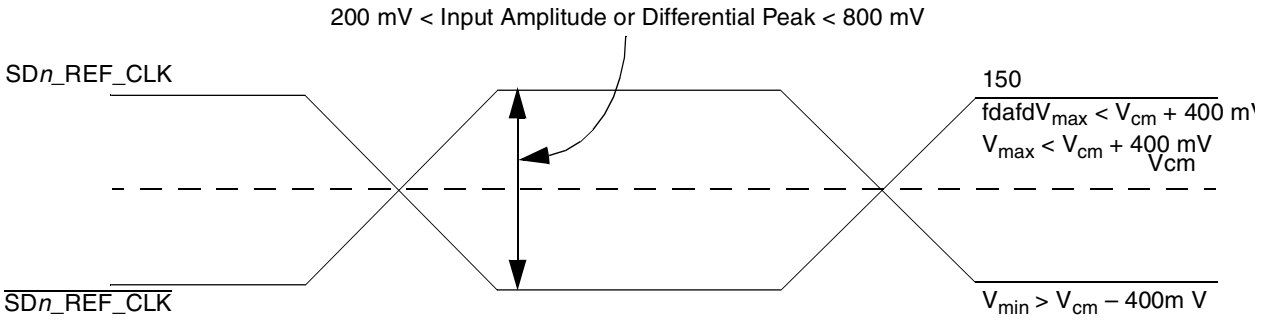

Figure 54. Differential Reference Clock Input DC Requirements (External AC-Coupled)

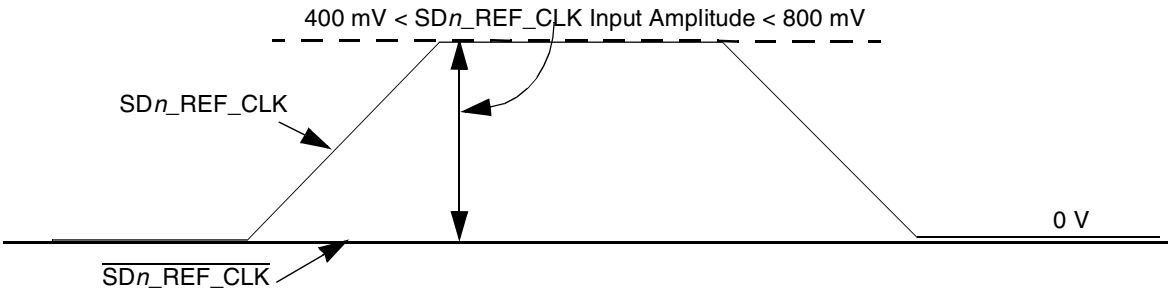

Figure 55. Single-Ended Reference Clock Input DC Requirements

21.2.3 Interfacing With Other Differential Signaling Levels

The following list provides information about interfacing with other differential signaling levels.

- With on-chip termination to SGND_SRDS*n* (xcorevss), the differential reference clocks inputs are HCSL (high-speed current steering logic) compatible DC-coupled.
- Many other low voltage differential type outputs like LVDS (low voltage differential signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 mV to 400 mV) for DC-coupled connection.
- LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

Table 73. Configurable Clock Units (continued)

Unit	Default Frequency	Options
PCI Express1, 2	csb_clk/3	Off, c*sb_clk, csb_clk/2, csb_clk/3*
SATA1, 2	csb_clk/3	Off, *csb_clk*

1 This only applies to I^2C1 (I^2C2 clock is not configurable).

This table provides the operating frequencies for the TePBGA II package under recommended operating conditions (see Table 3).

Table 74. Operating Frequencies for TePBGA II

Parameter[1]	Minimum Operating Frequency (MHz)	Maximum Operating Frequency (MHz)
e300 core frequency (*core_clk*)	333	800
Coherent system bus frequency (*csb_clk*)	133	400
DDR2 memory bus frequency (MCK)[1]	250	400
DDR1 memory bus frequency (MCK) [2]	167	333
Local bus frequency (LCLK*n*)[1]	—	133
Local bus controller frequency (*lbc_clk*)	—	400
PCI input frequency (CLKIN or PCI_CLK)	25	66
eTSEC frequency	133	400
Security encryption controller frequency	—	200
USB controller frequency	—	200
eSDHC controller frequency	—	200
PCI Express controller frequency	—	400
SATA controller frequency	—	200

Notes:
1. The CLKIN frequency, RCWLR[SPMF], and RCWLR[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[xCM] must be programmed such that the maximum internal operating frequency of the Security core, USB modules, SATA, and eSDHC will not exceed their respective value listed in this table.
2. The DDR data rate is 2× the DDR memory bus frequency.
3. The local bus frequency is ½, ¼, or 1/8 of the *lbiu_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWLR[LBCM]).

The thermal performance of a device cannot be adequately predicted from the junction to ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JB} \times P_D)$$

where:

T_A = ambient temperature for the package (°C)

$R_{\theta JB}$ = junction to board thermal resistance (°C/W) per JESD51-8

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

24.2.3 Experimental Determination of Junction Temperature

NOTE

The heat sink cannot be mounted on the package.

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction to ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

24.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

For the power values the device is expected to operate at, it is anticipated that a heat sink will be required. A preliminary estimate of heat sink performance can be obtained from the following first-cut approach.

The thermal resistance is expressed as the sum of a junction to case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)

$R_{\theta JC}$ = junction to case thermal resistance (°C/W)

$R_{\theta CA}$ = case to ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

This first-cut approach overestimates the heat sink size required, since heat flow through the board is not accounted for, which can be as much as one-third to one-half of the power generated in the package.

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling through the package and board and the convection cooling due to the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because of the wide variety of application environments, a single standard heat sink applicable to all cannot be specified.

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